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#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Not For New Designs
Core Processor	HCS12
Core Size	16-Bit
Speed	25MHz
Connectivity	CANbus, EBI/EMI, SCI, SPI
Peripherals	POR, PWM, WDT
Number of I/O	31
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2.35V ~ 5.5V
Data Converters	A/D 8x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
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#### Chapter 1 MC9S12C and MC9S12GC Device Overview (MC9S12C128)



The figure shows a useful map, which is not the map out of reset. After reset the map is: 0x0000–0x03FF: Register Space

0x0000-0x0FFF: 4K RAM (only 3K visible 0x0400-0x0FFF)

Flash erase sector size is 1024 bytes

#### Figure 1-2. MC9S12C128 and MC9S12GC128 User Configurable Memory Map



Address Space	Page Window Access	ROMHM	ECS	XAB19:14
0x0000-0x3FFF	N/A	N/A	1	0x3D
0x4000-0x7FFF	N/A	0	0	0x3E
	N/A	1	1	
0x8000-0xBFFF	External	N/A	1	PIX[5:0]
	Internal	N/A	0	
0xC000-0xFFFF	N/A	N/A	0	0x3F

Table 3-20. 48K Byte Physical FLASH/ROM Allocated

#### Table 3-21. 64K Byte Physical FLASH/ROM Allocated

Address Space	Page Window Access	ROMHM	ECS	XAB19:14
0x0000-0x3FFF	N/A	0	0	0x3D
	N/A	1	1	
0x4000-0x7FFF	N/A	0	0	0x3E
	N/A	1	1	
0x8000-0xBFFF	External	N/A	1	PIX[5:0]
	Internal	N/A	0	
0xC000-0xFFFF	N/A	N/A	0	0x3F



Chapter 4 Multiplexed External Bus Interface (MEBIV3)

# 4.3.2.5 Reserved Registers

Module Base + 0x0004

Starting address location affected by INITRG register setting.



### Figure 4-6. Reserved Register

Module Base + 0x0005

Starting address location affected by INITRG register setting.



### Figure 4-7. Reserved Register

Module Base + 0x0006 Starting address location affected by INITRG register setting.



### Figure 4-8. Reserved Register

Module Base + 0x0007

Starting address location affected by INITRG register setting.







Chapter 6 Background Debug Module (BDMV4) Block Description

# 6.3 Memory Map and Register Definition

A summary of the registers associated with the BDM is shown in Figure 6-2. Registers are accessed by host-driven communications to the BDM hardware using READ\_BD and WRITE\_BD commands. Detailed descriptions of the registers and associated bits are given in the subsections that follow.

# 6.3.1 Module Memory Map

Register Address	Use	Access
0xFF00	Reserved	—
0xFF01	BDM Status Register (BDMSTS)	R/W
0xFF02– 0xFF05	Reserved	—
0xFF06	BDM CCR Holding Register (BDMCCR)	R/W
0xFF07	BDM Internal Register Position (BDMINR)	R
0xFF08– 0xFF0B	Reserved	

Table	6-1.	INT	Memorv	Мар
	• • •			



Prescale Value	Total Divisor Value	Maximum Bus Clock <sup>(1)</sup>	Minimum Bus Clock <sup>(2)</sup>
00000	Divide by 2	4 MHz	1 MHz
00001	Divide by 4	8 MHz	2 MHz
00010	Divide by 6	12 MHz	3 MHz
00011	Divide by 8	16 MHz	4 MHz
00100	Divide by 10	20 MHz	5 MHz
00101	Divide by 12	24 MHz	6 MHz
00110	Divide by 14	28 MHz	7 MHz
00111	Divide by 16	32 MHz	8 MHz
01000	Divide by 18	36 MHz	9 MHz
01001	Divide by 20	40 MHz	10 MHz
01010	Divide by 22	44 MHz	11 MHz
01011	Divide by 24	48 MHz	12 MHz
01100	Divide by 26	52 MHz	13 MHz
01101	Divide by 28	56 MHz	14 MHz
01110	Divide by 30	60 MHz	15 MHz
01111	Divide by 32	64 MHz	16 MHz
10000	Divide by 34	68 MHz	17 MHz
10001	Divide by 36	72 MHz	18 MHz
10010	Divide by 38	76 MHz	19 MHz
10011	Divide by 40	80 MHz	20 MHz
10100	Divide by 42	84 MHz	21 MHz
10101	Divide by 44	88 MHz	22 MHz
10110	Divide by 46	92 MHz	23 MHz
10111	Divide by 48	96 MHz	24 MHz
11000	Divide by 50	100 MHz	25 MHz
11001	Divide by 52	104 MHz	26 MHz
11010	Divide by 54	108 MHz	27 MHz
11011	Divide by 56	112 MHz	28 MHz
11100	Divide by 58	116 MHz	29 MHz
11101	Divide by 60	120 MHz	30 MHz
11110	Divide by 62	124 MHz	31 MHz
11111	Divide by 64	128 MHz	32 MHz

#### Table 8-8. Clock Prescaler Values

1. Maximum ATD conversion clock frequency is 2 MHz. The maximum allowed bus clock frequency is shown in this column.

2. Minimum ATD conversion clock frequency is 500 kHz. The minimum allowed bus clock frequency is shown in this column.



# 8.7 Interrupts

The interrupt requested by the ATD10B8C is listed in Table 8-20. Refer to MCU specification for related vector address and priority.

Interrupt Source	CCR Mask	Local Enable
Sequence complete interrupt	I bit	ASCIE in ATDCTL2

### Table 8-20. ATD10B8C Interrupt Vectors

See Section 8.3.2, "Register Descriptions" for further details.



#### Chapter 9 Clocks and Reset Generator (CRGV4) Block Description

of 4 OSCCLK plus 4 PLLCLK cycles to make the transition. During the transition, all clocks freeze and CPU activity ceases.



Figure 9-18. Core Clock and Bus Clock Relationship

# 9.4.3 Clock Monitor (CM)

If no OSCCLK edges are detected within a certain time, the clock monitor within the oscillator block generates a clock monitor fail event. The CRGV4 then asserts self-clock mode or generates a system reset depending on the state of SCME bit. If the clock monitor is disabled or the presence of clocks is detected no failure is indicated by the oscillator block. The clock monitor function is enabled/disabled by the CME control bit.

# 9.4.4 Clock Quality Checker

The clock monitor performs a coarse check on the incoming clock signal. The clock quality checker provides a more accurate check in addition to the clock monitor.

A clock quality check is triggered by any of the following events:

- Power-on reset (POR)
- Low voltage reset (LVR)
- Wake-up from full stop mode (exit full stop)
- Clock monitor fail indication (CM fail)

A time window of 50000 VCO clock cycles<sup>1</sup> is called *check window*.

A number greater equal than 4096 rising OSCCLK edges within a *check window* is called *osc ok*. Note that *osc ok* immediately terminates the current *check window*. See Figure 9-19 as an example.



Figure 9-19. Check Window Example

1. VCO clock cycles are generated by the PLL when running at minimum frequency  $\mathrm{f}_{\mathrm{SCM}}$ 



Chapter 10 Freescale's Scalable Controller Area Network (S12MSCANV2)



#### Chapter 12 Pulse-Width Modulator (PWM8B6CV1) Block Description

• The channel is disabled

In this way, the output of the PWM will always be either the old waveform or the new waveform, not some variation in between. If the channel is not enabled, then writes to the period register will go directly to the latches as well as the buffer.

### NOTE

Reads of this register return the most recent value written. Reads do not necessarily return the value of the currently active period due to the double buffering scheme.

Reference Section 12.4.2.3, "PWM Period and Duty," for more information.

To calculate the output period, take the selected clock source period for the channel of interest (A, B, SA, or SB) and multiply it by the value in the period register for that channel:

- Left aligned output (CAEx = 0)
- PWMx period = channel clock period \* PWMPERx center aligned output (CAEx = 1)
- PWMx period = channel clock period \* (2 \* PWMPERx)

For boundary case programming values, please refer to Section 12.4.2.8, "PWM Boundary Cases."

Module Base + 0x0012





# Chapter 13 Serial Communications Interface (S12SCIV2) Block Description

# 13.1 Introduction

This block guide provide an overview of serial communication interface (SCI) module. The SCI allows asynchronous serial communications with peripheral devices and other CPUs.

# 13.1.1 Glossary

- IRQ Interrupt Request
- LSB Least Significant Bit
- MSB Most Significant Bit
- NRZ Non-Return-to-Zero
- RZI Return-to-Zero-Inverted
- RXD Receive Pin
- SCI Serial Communication Interface
- TXD Transmit Pin

# 13.1.2 Features

The SCI includes these distinctive features:

- Full-duplex operation
- Standard mark/space non-return-to-zero (NRZ) format
- 13-bit baud rate selection
- Programmable 8-bit or 9-bit data format
- Separately enabled transmitter and receiver
- Programmable transmitter output parity
- Two receiver wake up methods:
  - Idle line wake-up
  - Address mark wake-up
- Interrupt-driven operation with eight flags:
  - Transmitter empty

Address Offset	Use	Access
0x0000	Timer Input Capture/Output Compare Select (TIOS)	R/W
0x0001	Timer Compare Force Register (CFORC)	R/W <sup>(1)</sup>
0x0002	Output Compare 7 Mask Register (OC7M)	R/W
0x0003	Output Compare 7 Data Register (OC7D)	R/W
0x0004	Timer Count Register (TCNT(hi))	R/W <sup>(2)</sup>
0x0005	Timer Count Register (TCNT(lo))	R/W <sup>2</sup>
0x0006	Timer System Control Register1 (TSCR1)	R/W
0x0007	Timer Toggle Overflow Register (TTOV)	R/W
0x0008	Timer Control Register1 (TCTL1)	R/W
0x0009	Timer Control Register2 (TCTL2)	R/W
0x000A	Timer Control Register3 (TCTL3)	R/W
0x000B	Timer Control Register4 (TCTL4)	R/W
0x000C	Timer Interrupt Enable Register (TIE)	R/W
0x000D	Timer System Control Register2 (TSCR2)	R/W
0x000E	Main Timer Interrupt Flag1 (TFLG1)	R/W
0x000F	Main Timer Interrupt Flag2 (TFLG2)	R/W
0x0010	Timer Input Capture/Output Compare Register 0 (TC0(hi))	R/W <sup>(3)</sup>
0x0011	Timer Input Capture/Output Compare Register 0 (TC0(lo))	R/W <sup>3</sup>
0x0012	Timer Input Capture/Output Compare Register 1 (TC1(hi))	R/W <sup>3</sup>
0x0013	Timer Input Capture/Output Compare Register 1 (TC1(lo))	R/W <sup>3</sup>
0x0014	Timer Input Capture/Output Compare Register 2 (TC2(hi))	R/W <sup>3</sup>
0x0015	Timer Input Capture/Output Compare Register 2 (TC2(lo))	R/W <sup>3</sup>
0x0016	Timer Input Capture/Output Compare Register 3 (TC3(hi))	R/W <sup>3</sup>
0x0017	Timer Input Capture/Output Compare Register 3 (TC3(lo))	R/W <sup>3</sup>
0x0018	Timer Input Capture/Output Compare Register4 (TC4(hi))	R/W <sup>3</sup>
0x0019	Timer Input Capture/Output Compare Register 4 (TC4(lo))	R/W <sup>3</sup>
0x001A	Timer Input Capture/Output Compare Register 5 (TC5(hi))	R/W <sup>3</sup>
0x001B	Timer Input Capture/Output Compare Register 5 (TC5(lo))	R/W <sup>3</sup>
0x001C	Timer Input Capture/Output Compare Register 6 (TC6(hi))	R/W <sup>3</sup>
0x001D	Timer Input Capture/Output Compare Register 6 (TC6(Io))	R/W <sup>3</sup>
0x001E	Timer Input Capture/Output Compare Register 7 (TC7(hi))	R/W <sup>3</sup>
0x001F	Timer Input Capture/Output Compare Register 7 (TC7(lo))	R/W <sup>3</sup>
0x0020	16-Bit Pulse Accumulator Control Register (PACTL)	R/W
0x0021	Pulse Accumulator Flag Register (PAFLG)	R/W
0x0022	Pulse Accumulator Count Register (PACNT(hi))	R/W
0x0023	Pulse Accumulator Count Register (PACNT(lo))	R/W
0x0024 - 0x002C	Reserved	(4)
0x002D	Timer Test Register (TIMTST)	R/W <sup>2</sup>
0x002E - 0x002F	Reserved	4

### Table 15-2. TIM16B8CV1 Memory Map

1. Always read 0x0000.

2. Only writable in special modes (test\_mode = 1).

3. Write to these registers have no meaning or effect during input capture.

4. Write has no effect; return 0 on read



#### Table 15-15. TSCR2 Field Descriptions

Field	Description
7 TOI	Timer Overflow Interrupt Enable         0 Interrupt inhibited.         1 Hardware interrupt requested when TOF flag set.
3 TCRE	<ul> <li>Timer Counter Reset Enable — This bit allows the timer counter to be reset by a successful output compare 7 event. This mode of operation is similar to an up-counting modulus counter.</li> <li>Counter reset inhibited and counter free runs.</li> <li>Counter reset by a successful output compare 7.</li> <li>Note: If TC7 = 0x0000 and TCRE = 1, TCNT will stay at 0x0000 continuously. If TC7 = 0xFFFF and TCRE = 1, TOF will never be set when TCNT is reset from 0xFFFF to 0x0000.</li> <li>Note: TCRE=1 and TC7!=0, the TCNT cycle period will be TC7 x "prescaler counter width" + "1 Bus Clock", for a more detail explanation please refer to Section 15.4.3, "Output Compare</li> </ul>
2 PR[2:0]	<b>Timer Prescaler Select</b> — These three bits select the frequency of the timer prescaler clock derived from the Bus Clock as shown in Table 15-16.

PR2	PR1	PR0	Timer Clock
0	0	0	Bus Clock / 1
0	0	1	Bus Clock / 2
0	1	0	Bus Clock / 4
0	1	1	Bus Clock / 8
1	0	0	Bus Clock / 16
1	0	1	Bus Clock / 32
1	1	0	Bus Clock / 64
1	1	1	Bus Clock / 128

Table 15-16. Timer Clock Selection

### NOTE

The newly selected prescale factor will not take effect until the next synchronized edge where all prescale counter stages equal zero.

## 15.3.2.12 Main Timer Interrupt Flag 1 (TFLG1)

Module Base + 0x000E



Read: Anytime



# Chapter 17 16 Kbyte Flash Module (S12FTS16KV1)

# 17.1 Introduction

The FTS16K module implements a 16 Kbyte Flash (nonvolatile) memory. The Flash memory contains one array of 16 Kbytes organized as 256 rows of 64 bytes with an erase sector size of eight rows (512 bytes). The Flash array may be read as either bytes, aligned words, or misaligned words. Read access time is one bus cycle for byte and aligned word, and two bus cycles for misaligned words.

The Flash array is ideal for program and data storage for single-supply applications allowing for field reprogramming without requiring external voltage sources for program or erase. Program and erase functions are controlled by a command driven interface. The Flash module supports both mass erase and sector erase. An erased bit reads 1 and a programmed bit reads 0. The high voltage required to program and erase is generated internally. It is not possible to read from a Flash array while it is being erased or programmed.

### CAUTION

A Flash word must be in the erased state before being programmed. Cumulative programming of bits within a Flash word is not allowed.

## 17.1.1 Glossary

**Command Write Sequence** — A three-step MCU instruction sequence to program, erase, or erase verify the Flash array memory.

## 17.1.2 Features

- 16 Kbytes of Flash memory comprised of one 16 Kbyte array divided into 32 sectors of 512 bytes
- Automated program and erase algorithm
- Interrupts on Flash command completion and command buffer empty
- Fast sector erase and word program operation
- 2-stage command pipeline for faster multi-word program times
- Flexible protection scheme to prevent accidental program or erase
- Single power supply for Flash program and erase operations
- Security feature to prevent unauthorized access to the Flash array memory



To change the Flash protection that will be loaded on reset, the upper sector of the Flash array must be unprotected, then the Flash protection byte located at Flash address 0xFF0D must be written to.

A protected Flash sector is disabled by FPHDIS while the size of the protected sector is defined by FPHS[1:0] in the FPROT register.

Trying to alter any of the protected areas will result in a protect violation error and the PVIOL flag will be set in the FSTAT register (see Section 17.3.2.6). A mass erase of the whole Flash array is only possible when protection is fully disabled by setting the FPOPEN and FPHDIS bits. An attempt to mass erase a Flash array while protection is enabled will set the PVIOL flag in the FSTAT register.

#### Table 17-8. FPROT Field Descriptions

Field	Description
7 FPOPEN	<ul> <li>Protection Function for Program or Erase — The FPOPEN bit is used to either select an address range to be protected using the FPHDIS and FPHS[1:0] bits or to select the same address range to be unprotected as shown in Table 17-9.</li> <li>The FPHDIS bit allows a Flash address range to be unprotected</li> <li>The FPHDIS bit allows a Flash address range to be protected</li> </ul>
6 NV6	<b>Nonvolatile Flag Bit</b> — The NV6 bit should remain in the erased state for future enhancements.
5 FPHDIS	<ul> <li>Flash Protection Higher Address Range Disable — The FPHDIS bit determines whether there is a protected/unprotected area in the higher space of the Flash address map.</li> <li>0 Protection/unprotection enabled</li> <li>1 Protection/unprotection disabled</li> </ul>
4–3 FPHS[1:0]	Flash Protection Higher Address Size — The FPHS[1:0] bits determine the size of the protected/unprotected sector as shown in Table 17-10. The FPHS[1:0] bits can only be written to while the FPHDIS bit is set.
2–0 NV[2:0]	Nonvolatile Flag Bits — The NV[2:0] bits should remain in the erased state for future enhancements.

### Table 17-9. Flash Protection Function

FPOPEN	FPHDIS	FPHS1	FPHS0	Function <sup>(1)</sup>		
1	1	х	х	No protection		
1	0	х	х	Protect high range		
0	1	х	х	Full Flash array protected		
0	0	x	x	Unprotected high range		
1 Eor rongo	For rongo oizoo refer to Table 17 10					

1. For range sizes refer to Table 17-10.

#### Table 17-10. Flash Protection Higher Address Range

FPHS[1:0]	Address Range	Range Size
00	0xF800–0xFFFF	2 Kbytes
01	0xF000-0xFFFF	4 Kbytes
10	0xE000-0xFFFF	8 Kbytes
11	0xC000–0xFFFF	16 Kbytes



Field	Description
6, 5, 2, 0 CMDB[6:5] CMDB[2] CMDB[0]	Valid Flash commands are shown in Table 20-16. An attempt to execute any command other than those listed in Table 20-16 will set the ACCERR bit in the FSTAT register (see Section 20.3.2.6).

### Table 20-15. FCMD Field Descriptions

### Table 20-16. Valid Flash Command List

CMDB	NVM Command
0x05	Erase verify
0x20	Word program
0x40	Sector erase
0x41	Mass erase

### 20.3.2.8 RESERVED2

This register is reserved for factory testing and is not accessible to the user.

Module Base + 0x0007



#### Figure 20-14. RESERVED2

All bits read 0 and are not writable.

## 20.3.2.9 Flash Address Register (FADDR)

FADDRHI and FADDRLO are the Flash address registers.

Module Base + 0x0008





Chapter 20 96 Kbyte Flash Module (S12FTS96KV1)

# 20.4.1.2 Command Write Sequence

The Flash command controller is used to supervise the command write sequence to execute program, erase, and erase verify algorithms.

Before starting a command write sequence, the ACCERR and PVIOL flags in the FSTAT register must be clear and the CBEIF flag should be tested to determine the state of the address, data, and command buffers. If the CBEIF flag is set, indicating the buffers are empty, a new command write sequence can be started. If the CBEIF flag is clear, indicating the buffers are not available, a new command write sequence will overwrite the contents of the address, data, and command buffers.

A command write sequence consists of three steps which must be strictly adhered to with writes to the Flash module not permitted between the steps. However, Flash register and array reads are allowed during a command write sequence. The basic command write sequence is as follows:

- 1. Write to a valid address in the Flash array memory.
- 2. Write a valid command to the FCMD register.
- 3. Clear the CBEIF flag in the FSTAT register by writing a 1 to CBEIF to launch the command.

The address written in step 1 will be stored in the FADDR registers and the data will be stored in the FDATA registers. When the CBEIF flag is cleared in step 3, the CCIF flag is cleared by the Flash command controller indicating that the command was successfully launched. For all command write sequences, the CBEIF flag will set after the CCIF flag is cleared indicating that the address, data, and command buffers are ready for a new command write sequence to begin. A buffered command will wait for the active operation to be completed before being launched. Once a command is launched, the completion of the command operation is indicated by the setting of the CCIF flag in the FSTAT register. The CCIF flag will set upon completion of all active and buffered commands.



Chapter 20 96 Kbyte Flash Module (S12FTS96KV1)

### 20.4.1.3.3 Sector Erase Command

The sector erase operation will erase all addresses in a 1024 byte sector of the Flash array using an embedded algorithm.

An example flow to execute the sector erase operation is shown in Figure 20-26. The sector erase command write sequence is as follows:

- 1. Write to a Flash array address to start the command write sequence for the sector erase command. The Flash address written determines the sector to be erased while MCU address bits [9:0] and the data written are ignored.
- 2. Write the sector erase command, 0x40, to the FCMD register.
- 3. Clear the CBEIF flag in the FSTAT register by writing a 1 to CBEIF to launch the sector erase command.

If a Flash sector to be erased is in a protected area of the Flash array, the PVIOL flag in the FSTAT register will set and the sector erase command will not launch. Once the sector erase command has successfully launched, the CCIF flag in the FSTAT register will set after the sector erase operation has completed unless a new command write sequence has been buffered.



Field	Description
5 PVIOL	<ul> <li>Protection Violation — The PVIOL flag indicates an attempt was made to program or erase an address in a protected Flash array memory area. The PVIOL flag is cleared by writing a 1 to PVIOL. Writing a 0 to the PVIOL flag has no effect on PVIOL. While PVIOL is set, it is not possible to launch another command.</li> <li>0 No protection violation detected</li> <li>1 Protection violation has occurred</li> </ul>
4 ACCERR	Access Error — The ACCERR flag indicates an illegal access to the Flash array caused by either a violation of the command write sequence, issuing an illegal command (illegal combination of the CMDBx bits in the FCMD register) or the execution of a CPU STOP instruction while a command is executing (CCIF=0). The ACCERR flag is cleared by writing a 1 to ACCERR. Writing a 0 to the ACCERR flag has no effect on ACCERR. While ACCERR is set, it is not possible to launch another command. 0 No access error detected 1 Access error has occurred
2 BLANK	<ul> <li>Flash Array Has Been Verified as Erased — The BLANK flag indicates that an erase verify command has checked the Flash array and found it to be erased. The BLANK flag is cleared by hardware when CBEIF is cleared as part of a new valid command write sequence. Writing to the BLANK flag has no effect on BLANK.</li> <li>0 If an erase verify command has been requested, and the CCIF flag is set, then a 0 in BLANK indicates the array is not erased</li> <li>1 Flash array verifies as erased</li> </ul>
1 FAIL	Flag Indicating a Failed Flash Operation — In special modes, the FAIL flag will set if the erase verify operation fails (Flash array verified as not erased). Writing a 0 to the FAIL flag has no effect on FAIL. The FAIL flag is cleared by writing a 1 to FAIL. While FAIL is set, it is not possible to launch another command. 0 Flash operation completed without error 1 Flash operation failed
0 DONE	<ul> <li>Flag Indicating a Failed Operation is not Active — In special modes, the DONE flag will clear if a program, erase, or erase verify operation is active.</li> <li>0 Flash operation is active</li> <li>1 Flash operation is not active</li> </ul>

### Table 21-13. FSTAT Field Descriptions

#### Flash Command Register (FCMD) 21.3.2.7

The FCMD register defines the Flash commands.





Module Base + 0x0006



Bits CMDB6, CMDB5, CMDB2, and CMDB0 are readable and writable during a command write sequence while bits 7, 4, 3, and 1 read 0 and are not writable.



Conditio	ns are sh	own in Table A-4 with internal regulator enabled unless o	therwise noted	ł			
Num	С	Rating	Symbol	Min	Тур	Max	Unit
1	Р	Run Supply Current Single Chip,	I <sub>DD5</sub>	_	_	45	mA
2	P P C	Wait Supply current All modules enabled VDDR<4.9V, only RTI enabled <sup>2</sup> VDDR>4.9V, only RTI enabled	I <sub>DDW</sub>		 2.5 3.5	33 8 —	mA
6	СРСРСРСР	Pseudo Stop Current (RTI and COP disabled) <sup>23</sup> -40°C 27°C 85°C "C" Temp Option 100°C 105°C "V" Temp Option 120°C 125°C "M" Temp Option 140°C	I <sub>DDPS</sub> <sup>(1)</sup>		190 200 300 400 450 600 650 1000	 250  1400  1900  4800	μΑ
4	С С С С С	Pseudo Stop Current (RTI and COP enabled) <sup>(2) (3)</sup> -40°C 27°C 85°C 105°C 125°C	I <sub>DDPS</sub> <sup>1</sup>		370 500 590 780 1200	 	μΑ
5	СРСРСРСР	Stop Current <sup>3</sup> -40°C 27°C 85°C "C" Temp Option 100°C 105°C "V" Temp Option 120°C 125°C "M" Temp Option 140°C	I <sub>DDS</sub> 1		12 25 130 160 200 350 400 600	 100  1200  1700  4500	μΑ

#### Table A-9. Supply Current Characteristics for Other Family Members

1. STOP current measured in production test at increased junction temperature, hence for Temp Option "C" the test is carried out at 100°C although the Temperature specification is 85°C. Similarly for "v" and "M" options the temperature used in test lies 15°C above the temperature option specification.

2. PLL off

3. At those low power dissipation levels  $T_{\rm J}$  =  $T_{\rm A}$  can be assumed

Appendix A Electrical Characteristics



# A.7.3 Output Loads

### A.7.3.1 Resistive Loads

The on-chip voltage regulator is intended to supply the internal logic and oscillator circuits allows no external DC loads.

## A.7.3.2 Capacitive Loads

The capacitive loads are specified in Table A-24. Ceramic capacitors with X7R dielectricum are required.

Table A-24.	Voltage	Regulator —	<b>Capacitive Loads</b>
-------------	---------	-------------	-------------------------

Num	Characteristic	Symbol	Min	Typical	Max	Unit
1	V <sub>DD</sub> external capacitive load	C <sub>DDext</sub>	400	440	12000	nF
2	V <sub>DDPLL</sub> external capacitive load	C <sub>DDPLLext</sub>	90	220	5000	nF